Noboru Ohtani

List of Publications by Year
in descending order

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35 papers	726 citations	14 h-index (706676)	26 g-index (620720)
36 all docs	36 docs citations	36 times ranked	328 citing authors

#	Article	IF	Citations
1	Influence of the facet trace region in 4H-SiC substrate on the glide and propagation behaviors of basal plane dislocations in 4H-SiC homoepitaxial layers. Journal of Applied Physics, 2021, 130, 095702.	1.1	4
2	Undulated Step Structure on the (0001Â¯) Facet of Physical Vapor Transport-Grown 4H-SiC Crystals. Materials, 2021, 14, 6816.	1.3	1
3	Correlation between the stepâ€“terrace structure and the nitrogen doping variation observed on the (0001Â¯) facet of 4H-SiC crystals. Journal of Applied Physics, 2020, 128, .	1.1	8
4	Novel characterization method for the nitrogen doping concentration in heavily nitrogen-doped 4H-SiC crystals by Raman scattering microscopy. Japanese Journal of Applied Physics, 2020, 59, 051003.	0.8	9
5	Raman scattering microscopy imaging of basal plane stacking faults and associated partial dislocations in 4H-SiC crystals. Journal of Applied Physics, 2020, 127, .	1.1	8
6	Populations and propagation behaviors of pure and mixed threading screw dislocations in physical vapor transport grown 4H-SiC crystals investigated using X-ray topography. Japanese Journal of Applied Physics, 2020, 59, 091002.	0.8	8
7	Structural characterization of the grown crystal/seed interface of physical vapor transport grown 4H-SiC crystals using Raman microscopy and x-ray topography. Journal of Crystal Growth, 2019, 515, 58-65.	0.7	11
8	Formation and multiplication of basal plane dislocations during physical vapor transport growth of 4H-SiC crystals. Journal of Crystal Growth, 2019, 516, 51-56.	0.7	11
9	Silicon carbide. , 2019, , 129-179.		11
10	Stability of multiple Shockley type basal plane stacking faults in heavily nitrogen-doped 4H-SiC crystals. Journal of Crystal Growth, 2018, 498, 328-335.	0.7	3
11	Structural characterization of the growth front of physical vapor transport grown 4H-SiC crystals using X-ray topography. Journal of Crystal Growth, 2018, 499, 24-29.	0.7	9
12	Investigation of Run-to-Run Fluctuation in Growth Conditions of Physical Vapor Transport Growth of 4H-SiC Crystals. Materials Science Forum, 2018, 924, 19-22.	0.3	1
13	Formation of basal plane stacking faults on the (<mml:math) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 282 Td (xmlns:mml="http:/	0.7	9
14	Theoretical investigation of the formation of basal plane stacking faults in heavily nitrogen-doped 4H-SiC crystals. Journal of Applied Physics, 2016, 119, .	1.1	46
15	Crystallographic orientation dependence of SEM contrast revealed by SiC polytypes. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2015, 33, .	0.6	16
16	Surface morphology and step instability on the (0001Ì„)C facet of physical vapor transport-grown 4Hâ€“SiC single crystal boules. Journal of Crystal Growth, 2015, 431, 24-31.	0.7	23
17	Structural investigation of the seeding process for physical vapor transport growth of 4Hâ€“SiC single crystals. Journal of Crystal Growth, 2014, 386, 9-15.	0.7	18
18	Defect formation during the initial stage of physical vapor transport growth of 4Hâ€“SiC in the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si0003.gif" overflow="scroll"><mml:mo>[</mml:mo><mml:mn>11</mml:mn><mml:mover accent="true"><mml:mn>2</mml:mn><mml:mo>Â¯</mml:mo></mml:mover><mml:mn>0</mml:mn><mml:mo>]</mml:mo></mml:mat Journal of Crystal Growth, 2014, 408, 1-6.	0.7	14

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19	Tunneling Atomic Force Microscopy Studies on Surface Growth Pits Due to Dislocations in 4H-SiC Epitaxial Layers. Journal of Electronic Materials, 2012, 41, 2193-2196.	1.0	5
20	Analysis of Basal Plane Bending and Basal Plane Dislocations in 4H-SiC Single Crystals. Japanese Journal of Applied Physics, 2009, 48, 065503.	0.8	24
21	Investigation of heavily nitrogen-doped n+ 4Hâ€"SiC crystals grown by physical vapor transport. Journal of Crystal Growth, 2009, 311, 1475-1481.	0.7	66
22	Precise Determination of Thermal Expansion Coefficients Observed in 4H-SiC Single Crystals. Materials Science Forum, 2006, 527-529, 699-702.	0.3	14
23	Behavior of Basal Plane Dislocations in Hexagonal Silicon Carbide Single Crystals Grown by Physical Vapor Transport. Japanese Journal of Applied Physics, 2006, 45, 1738-1742.	0.8	14
24	Step bunching behaviour on the {0001} surface of hexagonal SiC. Journal of Crystal Growth, 2000, 210, 613-622.	0.7	55
25	Evolution of macrosteps on6Hâ^'SiC(0001):â€ƒImpurity-induced morphological instability of step trains. Physical Review B, 1999, 59, 4592-4595.	1.1	42
26	Stepped structure on the {0001} facet plane of Î±-SiC. Surface Science, 1998, 398, L303-L307.	0.8	16
27	Defect Formation During Sublimation Bulk Crystal Growth of Silicon Carbide. Materials Research Society Symposia Proceedings, 1998, 510, 37.	0.1	11
28	Impurity incorporation kinetics during modified-Lely growth of SiC. Journal of Applied Physics, 1998, 83, 4487-4490.	1.1	27
29	Sublimation growth of 6H- and 4H-SiC single crystals in the [11Â¯0 0] and [1 12Â¯0] directions. Journal of Crystal Growth, 1997, 181, 229-240.	0.7	95
30	Structural defects in Î±-SiC single crystals grown by the modified-Lely method. Journal of Crystal Growth, 1996, 167, 596-606.	0.7	72
31	Nitrogen Incorporation Kinetics during the Sublimation Growth of 6H and 4H SiC. Japanese Journal of Applied Physics, 1996, 35, 2240-2243.	0.8	39
32	Influence of the Seed Face Polarity on the Sublimation Growth of Î±-SiC. Japanese Journal of Applied Physics, 1995, 34, 4694-4698.	0.8	33
33	Structural and Electrical Characterization of the Initial Stage of Physical Vapor Transport Growth of 4H-SiC Crystals. Materials Science Forum, 0, 821-823, 90-95.	0.3	0
34	Investigation of the Surface Morphology and Stacking Fault Nucleation on the (000-1)C Facet of Heavily Nitrogen-Doped 4H-SiC Boules. Materials Science Forum, 0, 897, 189-192.	0.3	1
35	Annealing Behavior of Electrical Resistivities Perpendicular and Parallel to the Basal Plane of Heavily Nitrogen-Doped 4H-SiC Crystals. Materials Science Forum, 0, 924, 293-296.	0.3	1